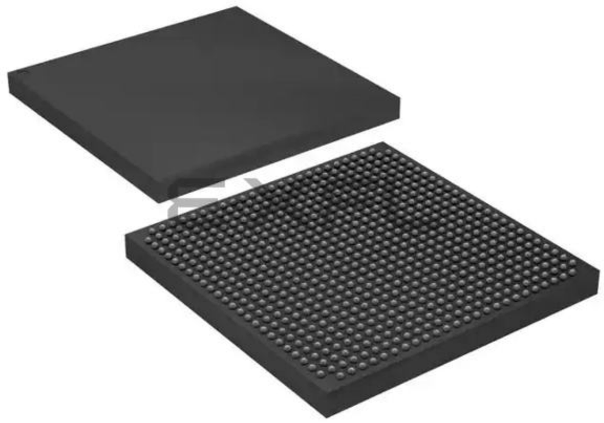
Intel - EP20K200FI672-3 Datasheet



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	832
Number of Logic Elements/Cells	8320
Total RAM Bits	106496
Number of I/O	-
Number of Gates	526000
Voltage - Supply	2.375V ~ 2.625V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-FBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k200fi672-3

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Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

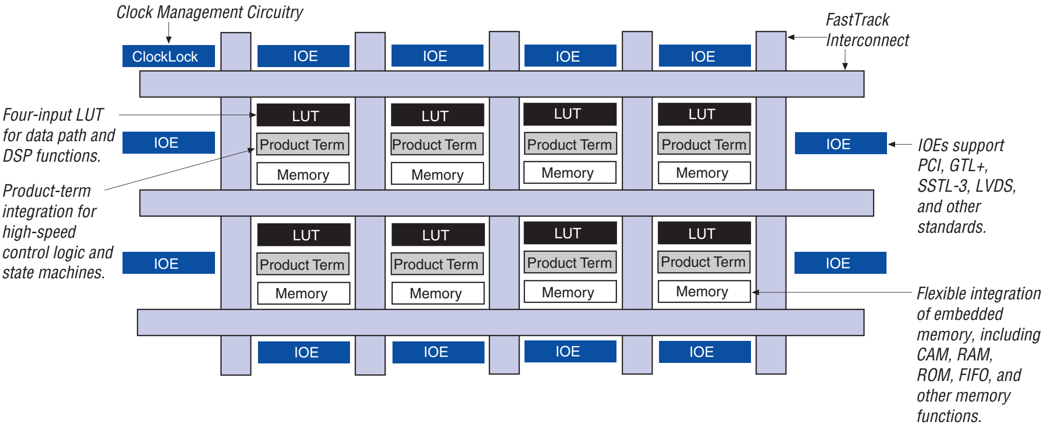
Functional Description

APEX 20K devices incorporate LUT-based logic, product-term-based logic, and memory into one device. Signal interconnections within APEX 20K devices (as well as to and from device pins) are provided by the FastTrack® Interconnect—a series of fast, continuous row and column channels that run the entire length and width of the device.

Each I/O pin is fed by an I/O element (IOE) located at the end of each row and column of the FastTrack Interconnect. Each IOE contains a bidirectional I/O buffer and a register that can be used as either an input or output register to feed input, output, or bidirectional signals. When used with a dedicated clock pin, these registers provide exceptional performance. IOEs provide a variety of features, such as 3.3-V, 64-bit, 66-MHz PCI compliance; JTAG BST support; slew-rate control; and tri-state buffers. APEX 20KE devices offer enhanced I/O support, including support for 1.8-V I/O, 2.5-V I/O, LVCMOS, LVTTL, LVPECL, 3.3-V PCI, PCI-X, LVDS, GTL+, SSTL-2, SSTL-3, HSTL, CTT, and 3.3-V AGP I/O standards.

The ESB can implement a variety of memory functions, including CAM, RAM, dual-port RAM, ROM, and FIFO functions. Embedding the memory directly into the die improves performance and reduces die area compared to distributed-RAM implementations. Moreover, the abundance of cascadable ESBs ensures that the APEX 20K device can implement multiple wide memory blocks for high-density designs. The ESB's high speed ensures it can implement small memory blocks without any speed penalty. The abundance of ESBs ensures that designers can create as many different-sized memory blocks as the system requires. Figure 1 shows an overview of the APEX 20K device.

Figure 1. APEX 20K Device Block Diagram



Logic Array Block

Each LAB consists of 10 LEs, the LEs' associated carry and cascade chains, LAB control signals, and the local interconnect. The local interconnect transfers signals between LEs in the same or adjacent LABs, IOEs, or ESBs. The Quartus II Compiler places associated logic within an LAB or adjacent LABs, allowing the use of a fast local interconnect for high performance. Figure 3 shows the APEX 20K LAB.

APEX 20K devices use an interleaved LAB structure. This structure allows each LE to drive two local interconnect areas. This feature minimizes use of the MegaLAB and FastTrack interconnect, providing higher performance and flexibility. Each LE can drive 29 other LEs through the fast local interconnect.

Figure 3. LAB Structure

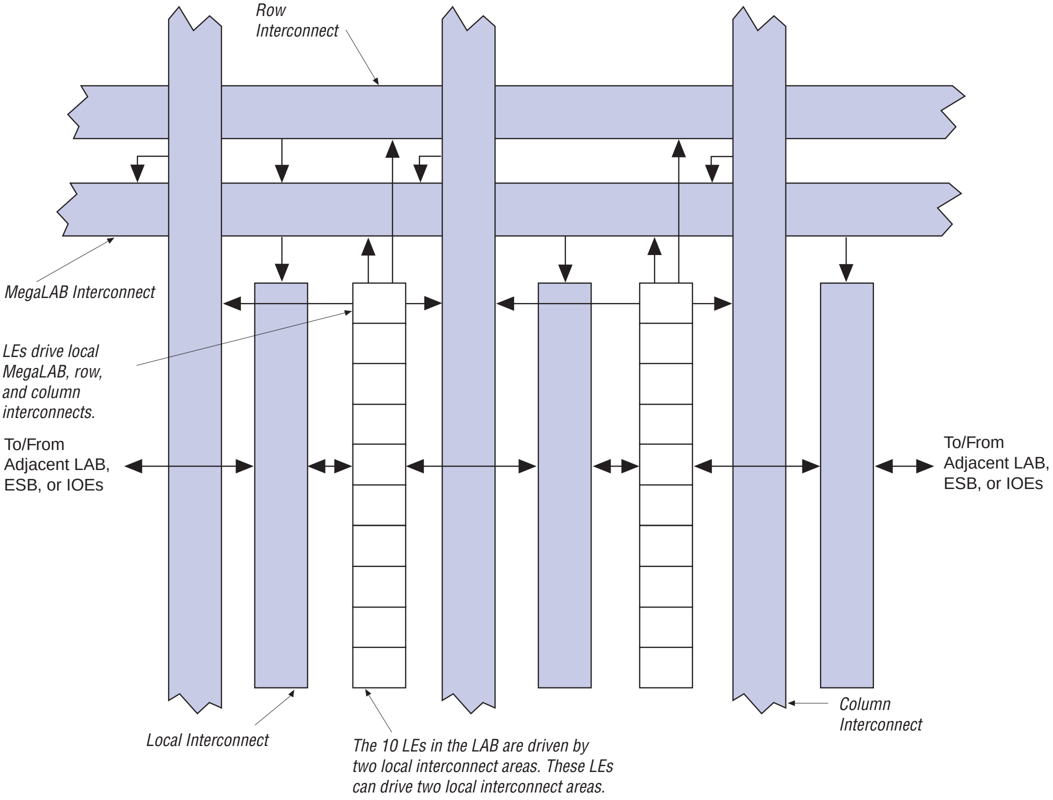
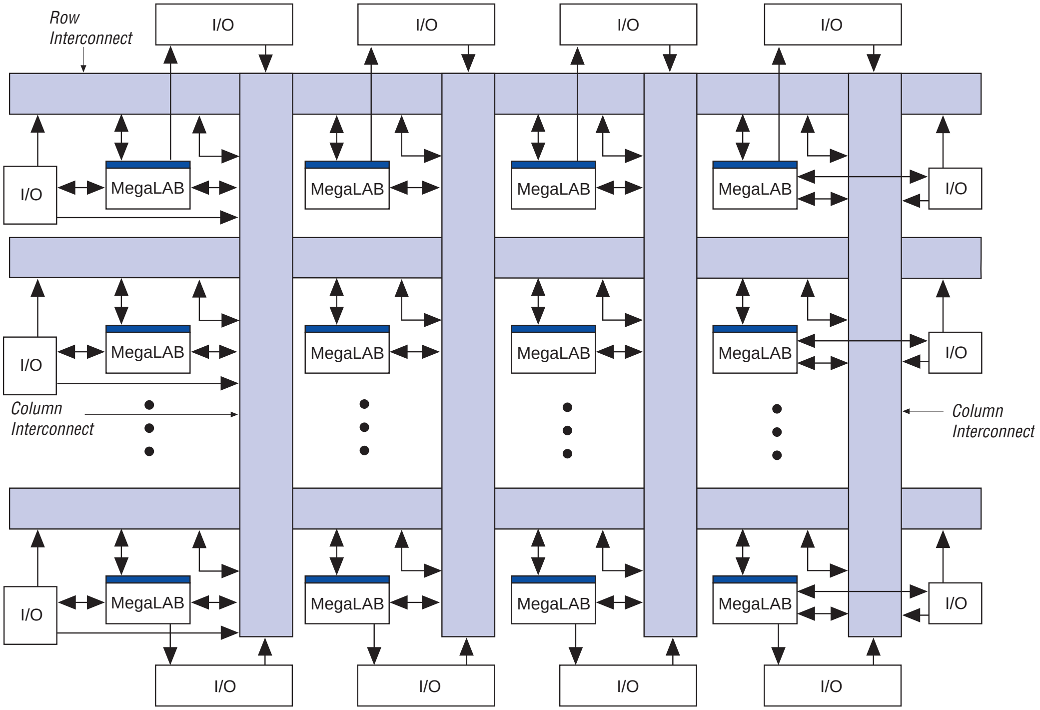


Figure 9. APEX 20K Interconnect Structure



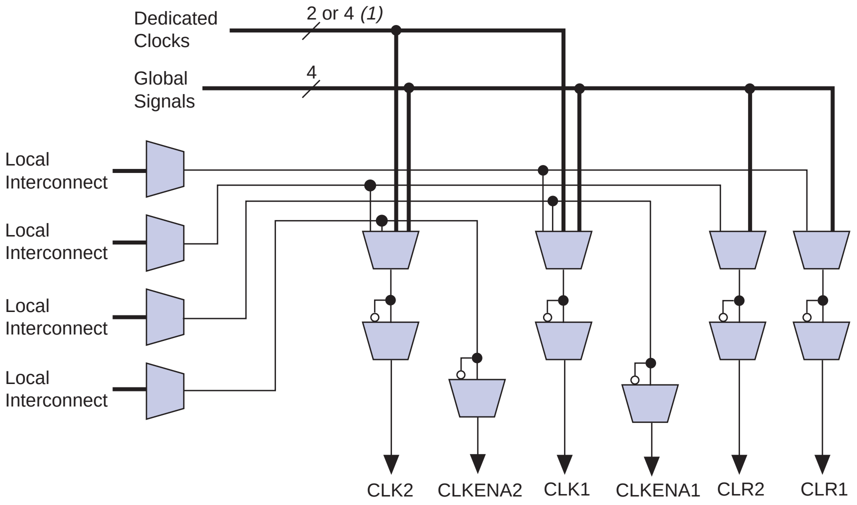
A row line can be driven directly by LEs, IOEs, or ESBs in that row. Further, a column line can drive a row line, allowing an LE, IOE, or ESB to drive elements in a different row via the column and row interconnect. The row interconnect drives the MegaLAB interconnect to drive LEs, IOEs, or ESBs in a particular MegaLAB structure.

A column line can be directly driven by LEs, IOEs, or ESBs in that column. A column line on a device's left or right edge can also be driven by row IOEs. The column line is used to route signals from one row to another. A column line can drive a row line; it can also drive the MegaLAB interconnect directly, allowing faster connections between rows.

Figure 10 shows how the FastTrack Interconnect uses the local interconnect to drive LEs within MegaLAB structures.

The programmable register also supports an asynchronous clear function. Within the ESB, two asynchronous clears are generated from global signals and the local interconnect. Each macrocell can either choose between the two asynchronous clear signals or choose to not be cleared. Either of the two clear signals can be inverted within the ESB. Figure 15 shows the ESB control logic when implementing product-terms.

Figure 15. ESB Product-Term Mode Control Logic



Note to Figure 15:

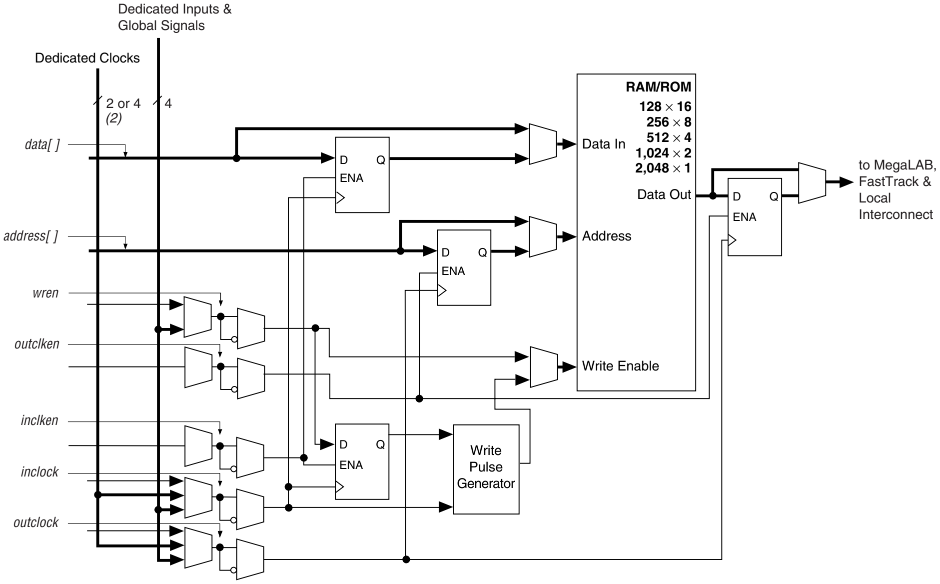
(1) APEX 20KE devices have four dedicated clocks.

Parallel Expanders

Parallel expanders are unused product terms that can be allocated to a neighboring macrocell to implement fast, complex logic functions. Parallel expanders allow up to 32 product terms to feed the macrocell `OR` logic directly, with two product terms provided by the macrocell and 30 parallel expanders provided by the neighboring macrocells in the ESB.

The Quartus II software Compiler can allocate up to 15 sets of up to two parallel expanders per set to the macrocells automatically. Each set of two parallel expanders incurs a small, incremental timing delay. Figure 16 shows the APEX 20K parallel expanders.

Figure 22. ESB in Single-Port Mode *Note (1)*



Notes to Figure 22:

(1) All registers can be asynchronously cleared by ESB local interconnect signals, global signals, or the chip-wide reset.
(2) APEX 20KE devices have four dedicated clocks.

Content-Addressable Memory

In APEX 20KE devices, the ESB can implement CAM. CAM can be thought of as the inverse of RAM. When read, RAM outputs the data for a given address. Conversely, CAM outputs an address for a given data word. For example, if the data `FA12` is stored in address `14`, the CAM outputs `14` when `FA12` is driven into it.

CAM is used for high-speed search operations. When searching for data within a RAM block, the search is performed serially. Thus, finding a particular data word can take many cycles. CAM searches all addresses in parallel and outputs the address storing a particular word. When a match is found, a match flag is set high. Figure 23 shows the CAM block diagram.

Implementing Logic in ROM

In addition to implementing logic with product terms, the ESB can implement logic functions when it is programmed with a read-only pattern during configuration, creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results, rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of ESBs. The large capacity of ESBs enables designers to implement complex functions in one logic level without the routing delays associated with linked LEs or distributed RAM blocks. Parameterized functions such as LPM functions can take advantage of the ESB automatically. Further, the Quartus II software can implement portions of a design with ESBs where appropriate.

Programmable Speed/Power Control

APEX 20K ESBs offer a high-speed mode that supports very fast operation on an ESB-by-ESB basis. When high speed is not required, this feature can be turned off to reduce the ESB's power dissipation by up to 50%. ESBs that run at low power incur a nominal timing delay adder. This Turbo Bit™ option is available for ESBs that implement product-term logic or memory functions. An ESB that is not used will be powered down so that it does not consume DC current.

Designers can program each ESB in the APEX 20K device for either high-speed or low-power operation. As a result, speed-critical paths in the design can run at high speed, while the remaining paths operate at reduced power.

I/O Structure

The APEX 20K IOE contains a bidirectional I/O buffer and a register that can be used either as an input register for external data requiring fast setup times, or as an output register for data requiring fast clock-to-output performance. IOEs can be used as input, output, or bidirectional pins. For fast bidirectional I/O timing, LE registers using local routing can improve setup times and OE timing. The Quartus II software Compiler uses the programmable inversion option to invert signals from the row and column interconnect automatically where appropriate. Because the APEX 20K IOE offers one output enable per pin, the Quartus II software Compiler can emulate open-drain operation efficiently.

The APEX 20K IOE includes programmable delays that can be activated to ensure zero hold times, minimum clock-to-output times, input IOE register-to-core register transfers, or core-to-output IOE register transfers. A path in which a pin directly drives a register may require the delay to ensure zero hold time, whereas a path in which a pin drives a register through combinatorial logic may not require the delay.

Table 10 describes the APEX 20K programmable delays and their logic options in the Quartus II software.

Table 10. APEX 20K Programmable Delay Chains

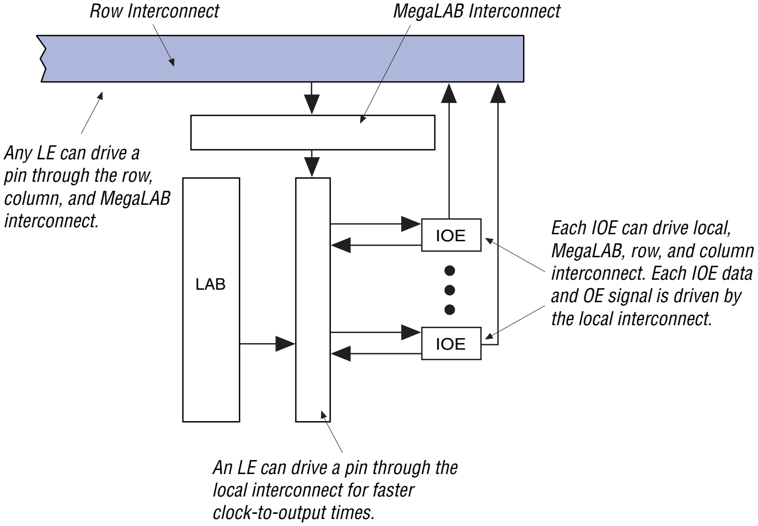
Programmable Delays	Quartus II Logic Option
Input pin to core delay	Decrease input delay to internal cells
Input pin to input register delay	Decrease input delay to input register
Core to output register delay	Decrease input delay to output register
Output register t_{CO} delay	Increase delay to output pin

The Quartus II software compiler can program these delays automatically to minimize setup time while providing a zero hold time. Figure 25 shows how fast bidirectional I/Os are implemented in APEX 20K devices.

The register in the APEX 20K IOE can be programmed to power-up high or low after configuration is complete. If it is programmed to power-up low, an asynchronous clear can control the register. If it is programmed to power-up high, the register cannot be asynchronously cleared or preset. This feature is useful for cases where the APEX 20K device controls an active-low input or another device; it prevents inadvertent activation of the input upon power-up.

Each IOE drives a row, column, MegaLAB, or local interconnect when used as an input or bidirectional pin. A row IOE can drive a local, MegaLAB, row, and column interconnect; a column IOE can drive the column interconnect. Figure 27 shows how a row IOE connects to the interconnect.

Figure 27. Row IOE Connection to the Interconnect



Any LE can drive a pin through the row, column, and MegaLAB interconnect.

Each IOE can drive local, MegaLAB, row, and column interconnect. Each IOE data and OE signal is driven by the local interconnect.

An LE can drive a pin through the local interconnect for faster clock-to-output times.

Table 15. APEX 20K ClockLock & ClockBoost Parameters for -1 Speed-Grade Devices (Part 2 of 2)

Symbol	Parameter	Min	Max	Unit
t_{SKEW}	Skew delay between related ClockLock/ClockBoost-generated clocks		500	ps
t_{JITTER}	Jitter on ClockLock/ClockBoost-generated clock *(5)*		200	ps
$t_{INCLKSTB}$	Input clock stability (measured between adjacent clocks)		50	ps

Notes to Table 15:
(1) The PLL input frequency range for the EP20K100-1X device for 1x multiplication is 25 MHz to 175 MHz.
(2) All input clock specifications must be met. The PLL may not lock onto an incoming clock if the clock specifications are not met, creating an erroneous clock within the device.
(3) During device configuration, the ClockLock and ClockBoost circuitry is configured first. If the incoming clock is supplied during configuration, the ClockLock and ClockBoost circuitry locks during configuration, because the lock time is less than the configuration time.
(4) The jitter specification is measured under long-term observation.
(5) If the input clock stability is 100 ps, t_{JITTER} is 250 ps.

Table 16 summarizes the APEX 20K ClockLock and ClockBoost parameters for -2 speed grade devices.

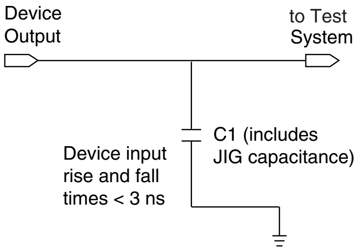
Table 16. APEX 20K ClockLock & ClockBoost Parameters for -2 Speed Grade Devices

Symbol	Parameter	Min	Max	Unit
f_{OUT}	Output frequency	25	170	MHz
f_{CLK1}	Input clock frequency (ClockBoost clock multiplication factor equals 1)	25	170	MHz
f_{CLK2}	Input clock frequency (ClockBoost clock multiplication factor equals 2)	16	80	MHz
f_{CLK4}	Input clock frequency (ClockBoost clock multiplication factor equals 4)	10	34	MHz
$t_{OUTDUTY}$	Duty cycle for ClockLock/ClockBoost-generated clock	40	60	%
f_{CLKDEV}	Input deviation from user specification in the Quartus II software (ClockBoost clock multiplication factor equals one) *(1)*		25,000 *(2)*	PPM
t_R	Input rise time		5	ns
t_F	Input fall time		5	ns
t_{LOCK}	Time required for ClockLock/ ClockBoost to acquire lock *(3)*		10	µs
t_{SKEW}	Skew delay between related ClockLock/ ClockBoost-generated clock	500	500	ps
t_{JITTER}	Jitter on ClockLock/ ClockBoost-generated clock *(4)*		200	ps
$t_{INCLKSTB}$	Input clock stability (measured between adjacent clocks)		50	ps

Table 18. APEX 20KE Clock Input & Output Parameters (Part 1 of 2) Note (1)

Symbol	Parameter	I/O Standard	-1X Speed Grade		-2X Speed Grade		Units
			Min	Max	Min	Max	
f_{VCO} (4)	Voltage controlled oscillator operating range		200	500	200	500	MHz
f_{CLOCK0}	`Clock0` PLL output frequency for internal use		1.5	335	1.5	200	MHz
f_{CLOCK1}	`Clock1` PLL output frequency for internal use		20	335	20	200	MHz
f_{CLOCK0_EXT}	Output clock frequency for external `clock0` output	3.3-V LVTTL	1.5	245	1.5	226	MHz
		2.5-V LVTTL	1.5	234	1.5	221	MHz
		1.8-V LVTTL	1.5	223	1.5	216	MHz
		GTL+	1.5	205	1.5	193	MHz
		SSTL-2 Class I	1.5	158	1.5	157	MHz
		SSTL-2 Class II	1.5	142	1.5	142	MHz
		SSTL-3 Class I	1.5	166	1.5	162	MHz
		SSTL-3 Class II	1.5	149	1.5	146	MHz
		LVDS	1.5	420	1.5	350	MHz
f_{CLOCK1_EXT}	Output clock frequency for external `clock1` output	3.3-V LVTTL	20	245	20	226	MHz
		2.5-V LVTTL	20	234	20	221	MHz
		1.8-V LVTTL	20	223	20	216	MHz
		GTL+	20	205	20	193	MHz
		SSTL-2 Class I	20	158	20	157	MHz
		SSTL-2 Class II	20	142	20	142	MHz
		SSTL-3 Class I	20	166	20	162	MHz
		SSTL-3 Class II	20	149	20	146	MHz
		LVDS	20	420	20	350	MHz

Figure 32. APEX 20K AC Test Conditions *Note (1)*



Note to Figure 32:

(1) Power supply transients can affect AC measurements. Simultaneous transitions of multiple outputs should be avoided for accurate measurement. Threshold tests must not be performed under AC conditions. Large-amplitude, fast-ground-current transients normally occur as the device outputs discharge the load capacitances. When these transients flow through the parasitic inductance between the device ground pin and the test system ground, significant reductions in observable noise immunity can result.

Operating Conditions

Tables 23 through 26 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 2.5-V APEX 20K devices.

Table 23. APEX 20K 5.0-V Tolerant Device Absolute Maximum Ratings *Notes (1), (2)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage	With respect to ground *(3)*	–0.5	3.6	V
V_{CCIO}			–0.5	4.6	V
V_I	DC input voltage		–2.0	5.75	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	° C
T_{AMB}	Ambient temperature	Under bias	–65	135	° C
T_J	Junction temperature	PQFP, RQFP, TQFP, and BGA packages, under bias		135	° C
		Ceramic PGA packages, under bias		150	° C

Table 24. APEX 20K 5.0-V Tolerant Device Recommended Operating Conditions *Note (2)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	*(4)*, *(5)*	2.375 (2.375)	2.625 (2.625)	V
V_{CCIO}	Supply voltage for output buffers, 3.3-V operation	*(4)*, *(5)*	3.00 (3.00)	3.60 (3.60)	V
	Supply voltage for output buffers, 2.5-V operation	*(4)*, *(5)*	2.375 (2.375)	2.625 (2.625)	V
V_I	Input voltage	*(3)*, *(6)*	–0.5	5.75	V
V_O	Output voltage		0	V_{CCIO}	V
T_J	Junction temperature	For commercial use	0	85	° C
		For industrial use	–40	100	° C
t_R	Input rise time			40	ns
t_F	Input fall time			40	ns

Table 25. APEX 20K 5.0-V Tolerant Device DC Operating Conditions (Part 1 of 2) *Notes (2), (7), (8)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level input voltage		1.7, 0.5 × V_{CCIO} *(9)*		5.75	V
V_{IL}	Low-level input voltage		–0.5		0.8, 0.3 × V_{CCIO} *(9)*	V
V_{OH}	3.3-V high-level TTL output voltage	I_{OH} = –8 mA DC, V_{CCIO} = 3.00 V *(10)*	2.4			V
	3.3-V high-level CMOS output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 3.00 V *(10)*	V_{CCIO} – 0.2			V
	3.3-V high-level PCI output voltage	I_{OH} = –0.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(10)*	0.9 × V_{CCIO}			V
	2.5-V high-level output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 2.30 V *(10)*	2.1			V
		I_{OH} = –1 mA DC, V_{CCIO} = 2.30 V *(10)*	2.0			V
		I_{OH} = –2 mA DC, V_{CCIO} = 2.30 V *(10)*	1.7			V

Table 26. APEX 20K 5.0-V Tolerant Device Capacitance *Notes (2), (14)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		12	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		8	pF

Notes to Tables 23 through 26:

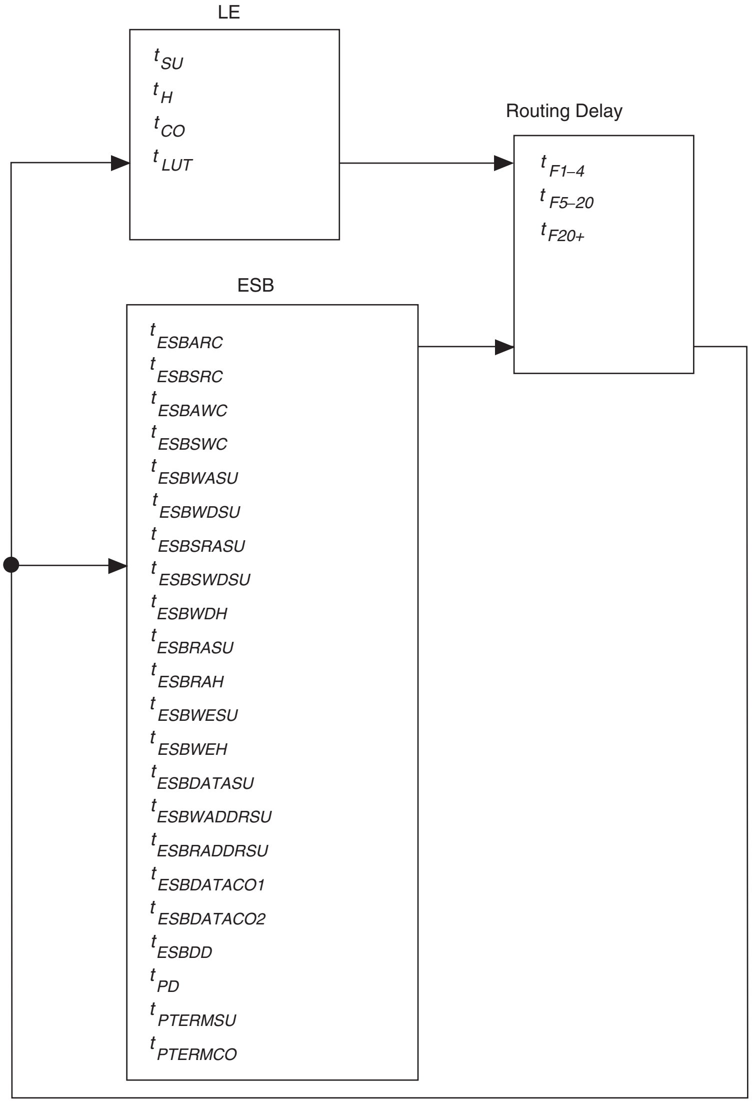
(1) See the *Operating Requirements for Altera Devices Data Sheet*.
(2) All APEX 20K devices are 5.0-V tolerant.
(3) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V or overshoot to 5.75 V for input currents less than 100 mA and periods shorter than 20 ns.
(4) Numbers in parentheses are for industrial-temperature-range devices.
(5) Maximum V_{CC} rise time is 100 ms, and V_{CC} must rise monotonically.
(6) All pins, including dedicated inputs, clock I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.
(7) Typical values are for T_A= 25° C, V_{CCINT} = 2.5 V, and V_{CCIO} = 2.5 or 3.3 V.
(8) These values are specified in the APEX 20K device recommended operating conditions, shown in Table 26 on page 62.
(9) The APEX 20K input buffers are compatible with 2.5-V and 3.3-V (LVTTL and LVCMOS) signals. Additionally, the input buffers are 3.3-V PCI compliant when V_{CCIO} and V_{CCINT} meet the relationship shown in Figure 33 on page 68.
(10) The I_{OH} parameter refers to high-level TTL, PCI or CMOS output current.
(11) The I_{OL} parameter refers to low-level TTL, PCI, or CMOS output current. This parameter applies to open-drain pins as well as output pins.
(12) This value is specified for normal device operation. The value may vary during power-up.
(13) Pin pull-up resistance values will be lower if an external source drives the pin higher than V_{CCIO}.
(14) Capacitance is sample-tested only.

Tables 27 through 30 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 1.8-V APEX 20KE devices.

Table 27. APEX 20KE Device Absolute Maximum Ratings *Note (1)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage	With respect to ground *(2)*	–0.5	2.5	V
V_{CCIO}			–0.5	4.6	V
V_I	DC input voltage		–0.5	4.6	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	° C
T_{AMB}	Ambient temperature	Under bias	–65	135	° C
T_J	Junction temperature	PQFP, RQFP, TQFP, and BGA packages, under bias		135	° C
		Ceramic PGA packages, under bias		150	° C

Figure 37. APEX 20KE f_{MAX} Timing Model



Tables 40 through 42 show the f_{MAX} timing parameters for EP20K100, EP20K200, and EP20K400 APEX 20K devices.

Table 40. EP20K100 f_{MAX} Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Units
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.5		0.6		0.8		ns
t_{H}	0.7		0.8		1.0		ns
t_{CO}		0.3		0.4		0.5	ns
t_{LUT}		0.8		1.0		1.3	ns
t_{ESBRC}		1.7		2.1		2.4	ns
t_{ESBWC}		5.7		6.9		8.1	ns
$t_{ESBWESU}$	3.3		3.9		4.6		ns
$t_{ESBDATASU}$	2.2		2.7		3.1		ns
$t_{ESBDATAH}$	0.6		0.8		0.9		ns
$t_{ESBADDRSU}$	2.4		2.9		3.3		ns
$t_{ESBDATACO1}$		1.3		1.6		1.8	ns
$t_{ESBDATACO2}$		2.6		3.1		3.6	ns
t_{ESBDD}		2.5		3.3		3.6	ns
t_{PD}		2.5		3.0		3.6	ns
$t_{PTERMSU}$	2.3		2.6		3.2		ns
$t_{PTERMCO}$		1.5		1.8		2.1	ns
t_{F1-4}		0.5		0.6		0.7	ns
t_{F5-20}		1.6		1.7		1.8	ns
t_{F20+}		2.2		2.2		2.3	ns
t_{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns
t_{CLRP}	0.3		0.4		0.4		ns
t_{PREP}	0.5		0.5		0.5		ns
t_{ESBCH}	2.0		2.5		3.0		ns
t_{ESBCL}	2.0		2.5		3.0		ns
t_{ESBWP}	1.6		1.9		2.2		ns
t_{ESBRP}	1.0		1.3		1.4		ns

Table 41. EP20K200 f_{MAX} Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Units
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.5		0.6		0.8		ns
t_{H}	0.7		0.8		1.0		ns
t_{CO}		0.3		0.4		0.5	ns
t_{LUT}		0.8		1.0		1.3	ns
t_{ESBRC}		1.7		2.1		2.4	ns
t_{ESBWC}		5.7		6.9		8.1	ns
$t_{ESBWESU}$	3.3		3.9		4.6		ns
$t_{ESBDATASU}$	2.2		2.7		3.1		ns
$t_{ESBDATAH}$	0.6		0.8		0.9		ns
$t_{ESBADDRSU}$	2.4		2.9		3.3		ns
$t_{ESBDATACO1}$		1.3		1.6		1.8	ns
$t_{ESBDATACO2}$		2.6		3.1		3.6	ns
t_{ESBDD}		2.5		3.3		3.6	ns
t_{PD}		2.5		3.0		3.6	ns
$t_{PTERMSU}$	2.3		2.7		3.2		ns
$t_{PTERMCO}$		1.5		1.8		2.1	ns
t_{F1-4}		0.5		0.6		0.7	ns
t_{F5-20}		1.6		1.7		1.8	ns
t_{F20+}		2.2		2.2		2.3	ns
t_{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns
t_{CLRP}	0.3		0.4		0.4		ns
t_{PREP}	0.4		0.5		0.5		ns
t_{ESBCH}	2.0		2.5		3.0		ns
t_{ESBCL}	2.0		2.5		3.0		ns
t_{ESBWP}	1.6		1.9		2.2		ns
t_{ESBRP}	1.0		1.3		1.4		ns

Tables 55 through 60 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K60E APEX 20KE devices.

Table 55. EP20K60E f_{MAX} LE Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.17		0.15		0.16		ns
t_{H}	0.32		0.33		0.39		ns
t_{CO}		0.29		0.40		0.60	ns
t_{LUT}		0.77		1.07		1.59	ns

Table 68. EP20K160E f_{MAX} ESB Timing Microparameters							
Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.65		2.02		2.11	ns
t_{ESBSRC}		2.21		2.70		3.11	ns
t_{ESBAWC}		3.04		3.79		4.42	ns
t_{ESBSWC}		2.81		3.56		4.10	ns
$t_{ESBWASU}$	0.54		0.66		0.73		ns
t_{ESBWAH}	0.36		0.45		0.47		ns
$t_{ESBWDSU}$	0.68		0.81		0.94		ns
t_{ESBWDH}	0.36		0.45		0.47		ns
$t_{ESBRASU}$	1.58		1.87		2.06		ns
t_{ESBRAH}	0.00		0.00		0.01		ns
$t_{ESBWESU}$	1.41		1.71		2.00		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	-0.02		-0.03		0.09		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.14		0.17		0.35		ns
$t_{ESBRADDRSU}$	0.21		0.27		0.43		ns
$t_{ESBDATACO1}$		1.04		1.30		1.46	ns
$t_{ESBDATACO2}$		2.15		2.70		3.16	ns
t_{ESBDD}		2.69		3.35		3.97	ns
t_{PD}		1.55		1.93		2.29	ns
$t_{PTERMSU}$	1.01		1.23		1.52		ns
$t_{PTERMCO}$		1.06		1.32		1.04	ns

Table 80. EP20K300E f_{MAX} ESB Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.79		2.44		3.25	ns
t_{ESBSRC}		2.40		3.12		4.01	ns
t_{ESBAWC}		3.41		4.65		6.20	ns
t_{ESBSWC}		3.68		4.68		5.93	ns
$t_{ESBWASU}$	1.55		2.12		2.83		ns
t_{ESBWAH}	0.00		0.00		0.00		ns
$t_{ESBWDSU}$	1.71		2.33		3.11		ns
t_{ESBWDH}	0.00		0.00		0.00		ns
$t_{ESBRASU}$	1.72		2.34		3.13		ns
t_{ESBRAH}	0.00		0.00		0.00		ns
$t_{ESBWESU}$	1.63		2.36		3.28		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	0.07		0.39		0.80		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.27		0.67		1.17		ns
$t_{ESBRADDRSU}$	0.34		0.75		1.28		ns
$t_{ESBDATACO1}$		1.03		1.20		1.40	ns
$t_{ESBDATACO2}$		2.33		3.18		4.24	ns
t_{ESBDD}		3.41		4.65		6.20	ns
t_{PD}		1.68		2.29		3.06	ns
$t_{PTERMSU}$	0.96		1.48		2.14		ns
$t_{PTERMCO}$		1.05		1.22		1.42	ns

Table 81. EP20K300E f_{MAX} Routing Delays

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.22		0.24		0.26	ns
t_{F5-20}		1.33		1.43		1.58	ns
t_{F20+}		3.63		3.93		4.35	ns

Table 90. EP20K400E External Bidirectional Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	2.93		3.23		3.44		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	5.25	2.00	5.79	2.00	6.32	ns
$t_{XZBIDIR}$		5.95		6.77		7.12	ns
$t_{ZXBIDIR}$		5.95		6.77		7.12	ns
$t_{INSUBIDIRPLL}$	4.31		4.76		-		ns
$t_{INHBIDIRPLL}$	0.00		0.00		-		ns
$t_{OUTCOBIDIRPLL}$	0.50	2.25	0.50	2.45	-	-	ns
$t_{XZBIDIRPLL}$		2.94		3.43		-	ns
$t_{ZXBIDIRPLL}$		2.94		3.43		-	ns

Tables 91 through 96 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K600E APEX 20KE devices.

Table 91. EP20K600E f_{MAX} LE Timing Microparameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.16		0.16		0.17		ns
t_{H}	0.29		0.33		0.37		ns
t_{CO}		0.65		0.38		0.49	ns
t_{LUT}		0.70		1.00		1.30	ns